



NTE71 Silicon NPN Transistor High Current Amp, Fast Switch

Description:

The NTE71 is silicon NPN transistor in a TO63 stud mount package utilizing C2R processing that provides surface stabilization for high voltage operation and enhances long term reliability.

Absolute Maximum Ratings:

Collector–Base Voltage, V_{CBO}	150V
Collector–Emitter Voltage, V_{CEO}	150V
Emitter–Base VOltage, V_{EBO}	10V
Continuous Collector Current, I_C	20A
Continuous Base Current, I_B	4.5A
Total Power Dissipation ($T_C = +25^\circ\text{C}$), P_D	200W
Storage Temperature Range, T_{stg}	–65° to +200°C

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector–Emitter Sustaining Voltage	$V_{(BR)CEO(sus)}$	$I_C = 100\text{mA}$	150	–	–	V
Emitte Cutoff Current	I_{EBO}	$V_{EB} = 10\text{V}$	–	–	250	μA
Collector Cutoff Current	I_{CEX}	$V_{CE} = 150\text{V}, V_{BE} = -1.5\text{V}$	–	–	2	mA
		$V_{CE} = 150\text{V}, V_{BE} = -1.5\text{V}, T_C = +150^\circ\text{C}$	–	–	20	mA
ON Characteristics (Note 1)						
DC Current Gain	h_{FE}	$V_{CE} = 3\text{V}, I_C = 10\text{A}$	10	–	50	
Collector Saturation Voltage	$V_{CE(\text{sat})}$	$I_C = 10\text{A}, I_B = 1.5\text{A}$	–	–	1.5	V
Base–Emitter Voltage	V_{BE}	$I_C = 10\text{A}, I_B = 1.5\text{A}$	–	–	2.5	V

Note 1. Pulse test: Pulse Width = 300μs, Duty Cycle ≤ 2%.

Electrical Characteristics (Cont'd): ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Dynamic Characteristics						
Small-Signal Current Gain	h_{fe}	$V_{CE} = 3\text{V}$, $I_C = 10\text{A}$, $f = 1\text{MHz}$	0.6	—	—	
Turn-On Time	t_{on}	$V_{CC} = 30\text{V}$, $I_C = 10\text{A}$, $I_{B1} = 1.5\text{A}$,	—	—	3.5	μs
Turn-Off Time	t_{off}	$I_{B2} = 1.5\text{A}$	—	—	12.0	μs
Rise Time	t_r		—	—	3.5	μs
Storage Time	t_s		—	—	6.0	μs
Fall Time	t_f		—	—	6.0	μs

